

# SOI SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

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Inventor(s): YAMAZAKI HIROSHI +

Applicant(s): FUJITSU LTD +

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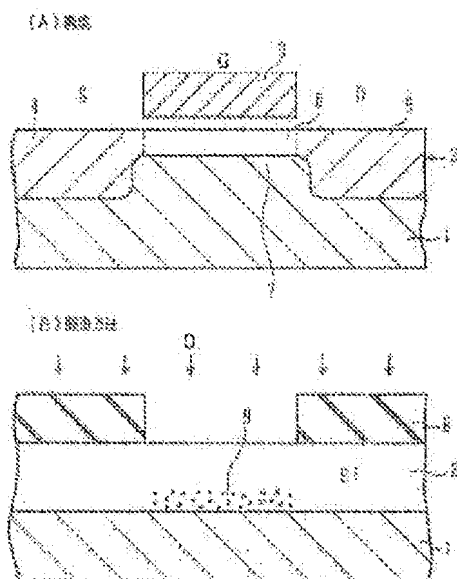
- European:

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## Abstract of JP 5121744 (A)

**PURPOSE:** To provide an SOI semiconductor device of a structure, wherein the thickness of a semiconductor layer under a gate electrode constituting a channel region is made thin sufficiently and the resistances of source and drain regions can be kept low. **CONSTITUTION:** An SOI semiconductor device has an insulative region 1 provided with a bump-shaped oxide region 7 at its one part, a silicon layer 2 lying across the region 7 on the region 1 and whose thickness on the region 7 is smaller than that of the regions on both sides of the region 7, and a gate electrode 3 formed over the region 7 and on the layer 2.



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